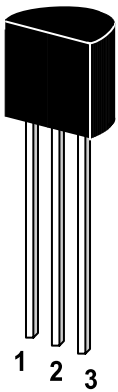


ST 2N6517

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NPN Silicon Epitaxial Planar Transistor
for switching and AF amplifier applications.

On special request, these transistors can be manufactured in different pin configurations.

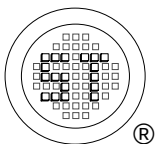


1. Emitter 2. Base 3. Collector

TO-92 Plastic Package
Weight approx. 0.19g

Absolute Maximum Ratings ($T_a = 25^{\circ}\text{C}$)

	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	350	V
Collector Emitter Voltage	V_{CEO}	350	V
Emitter Base Voltage	V_{EBO}	6	V
Collector Current	I_C	500	mA
Power Dissipation	P_{tot}	625	mW
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_S	-55 to +150	$^{\circ}\text{C}$



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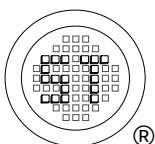
Dated : 07/12/2002

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Characteristics at $T_{amb}=25^{\circ}C$

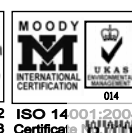
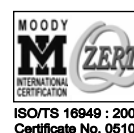
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	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain					
at $V_{CE}=10V$, $I_C=1mA$	h_{FE}	20	-	-	-
at $V_{CE}=10V$, $I_C=10mA$	h_{FE}	30	-	-	-
at $V_{CE}=10V$, $I_C=30mA$	h_{FE}	30	-	200	-
at $V_{CE}=10V$, $I_C=50mA$	h_{FE}	20	-	200	-
at $V_{CE}=10V$, $I_C=100mA$	h_{FE}	15	-	-	-
Collector Base Breakdown Voltage					
at $I_C=100\mu A$	BV_{CBO}	350	-	-	V
Collector Emitter Breakdown Voltage					
at $I_C=1mA$	BV_{CEO}	350	-	-	V
Emitter Base Breakdown Voltage					
at $I_E=10\mu A$	BV_{EBO}	6	-	-	V
Collector Cutoff Current					
at $V_{CB}=250V$	I_{CBO}	-	-	50	nA
Emitter Cutoff Current					
at $V_{EB}=5V$	I_{EBO}	-	-	50	nA
Collector Base Capacitance					
at $V_{CB}=20V$, $f=1MHz$	C_{cb}	-	-	6	pF
Base Emitter Saturation Voltage					
at $I_C=10mA$, $I_B=1mA$	$V_{BE(sat)}$	-	-	0.75	V
at $I_C=20mA$, $I_B=2mA$	$V_{BE(sat)}$	-	-	0.85	V
at $I_C=30mA$, $I_B=3mA$	$V_{BE(sat)}$	-	-	0.9	V
Collector Emitter Saturation Voltage					
at $I_C=10mA$, $I_B=1mA$	$V_{CE(sat)}$	-	-	0.3	V
at $I_C=20mA$, $I_B=2mA$	$V_{CE(sat)}$	-	-	0.35	V
at $I_C=30mA$, $I_B=3mA$	$V_{CE(sat)}$	-	-	0.5	V
at $I_C=50mA$, $I_B=5mA$	$V_{CE(sat)}$	-	-	1	V
Base Emitter On Voltage					
at $V_{CE}=10V$, $I_C=100mA$	$V_{BE(on)}$	-	-	2	V
Current Gain Bandwidth Product					
at $V_{CE}=20V$, $I_C=10mA$, $f=20MHz$	f_T	40	-	200	MHz



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